



CHENMKO ENTERPRISE CO., LTD

SURFACE MOUNT

Power Management (Dual Transistor)

Tr1: VOLTAGE 12 Volts CURRENT 0.5 Ampere
 DTr2: VOLTAGE 50 Volts CURRENT 30 mAmpere

CHUMF8PT

Lead free devices

APPLICATION

- * Power management circuit

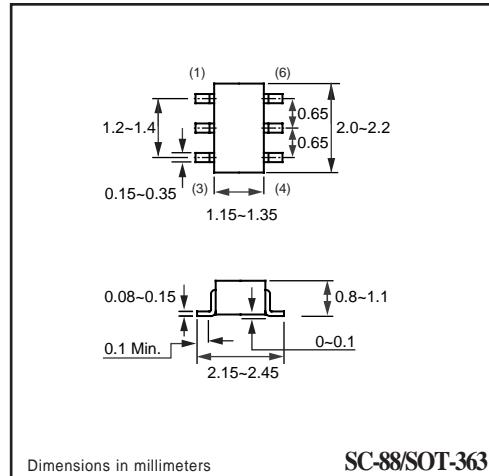
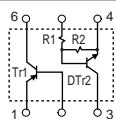
FEATURE

- * Small surface mounting type. (SC-88/SOT-363)
- * Power switching circuit in a single package.
- * Mounting cost and area can be cut in half.
- * Both the 2SC5585 & CHDTC144E in one package.
- * Built in bias resistor(R1=47kΩ, Typ.)



SC-88/SOT-363

CIRCUIT



SC-88/SOT-363

2SC5585 LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	Collector-base voltage		—	15	V
V _{CEO}	Collector-emitter voltage		—	12	V
V _{EBO}	Emitter-base voltage		—	6	V
I _c	DC Output current		—	500	mA
I _{cp}		NOTE.1	—	1000	
P _c	Total power dissipation	NOTE.2	—	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		—	150	°C

Note

1. Single pulse Pw=1ms
 2. 120mW per element must not be exceeded.
- Each terminal mounted on a recommended land.

CHDTC144E LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Vcc	Supply voltage		–	50	V
VIN	Input voltage		-10	+40	V
Io	DC Output current IC(Max.)		–	30	mA
		NOTE.1	–	100	
Pc	Power dissipation	NOTE.2	–	150	mW
TSTG	Storage temperature		-55	+150	°C
TJ	Junction temperature		–	150	°C

Note

1. Characteristics of built-in transistor.
2. Each terminal mounter on a recommended land.

2SC5585 CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
BVCEO	Collector-emitter breakdown voltage	Ic=1mA	12	–	–	V
BVcbo	Collector-base breakdown voltage	Ic=10uA	15	–	–	V
BVEBO	Emitter-base breakdown voltage	Ie=10uA	6	–	–	V
Icbo	Collector cut-off current	Vcb=15V	–	–	100	nA
Ieb0	Emitter cut-off current	Veb=6V	–	–	100	nA
hFE	DC current gain	Vce=2V, Ic=10mA	270	–	680	–
Vce(sat)	Collector-emitter saturation voltage	Ic=200mA, Ib=10mA	–	100	250	mV
Cob	Collector output capacitance	Vcb=10V, Ie=0mA, f=1MHz	–	7.5	–	pF
fT	Transition frequency	Vce=2V, Ie=-10mA, f=100MHz	–	320	–	MHz

Note

1. Pulse test: tp≤300uS; δ≤0.02.

CHDTC144E CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Vloff	Input off voltage	Io=100uA; Vcc=5.0V	0.5	–	–	V
Vi(on)	Input on voltage	Io=2mA; Vo=0.3V	–	–	3.0	V
VO(on)	Output voltage	Io=10mA; II=0.5mA	–	0.1	0.3	V
II	Input current	Vi=5V	–	–	180	uA
IC(off)	Output current	Vi=0V; Vcc=50V	–	–	500	nA
G1	DC current gain	Io=5mA; Vo=5.0V	68	–	–	–
R1	Input resistor		32.9	47	61.1	KΩ
R2/R1	Resistor ratio		0.8	1.0	1.2	–
fT	Transition frequency	IE=-5mA, Vce=10.0V f=100MHz	–	250	–	MHz

Note

Pulse test: tp≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHUMF8PT)

2SC5585 Typical Electrical Characteristics

Fig.1 Ground emitter propagation characteristics

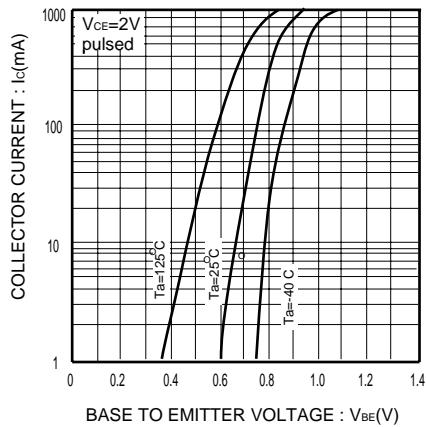


Fig.2 DC current gain vs. collector current

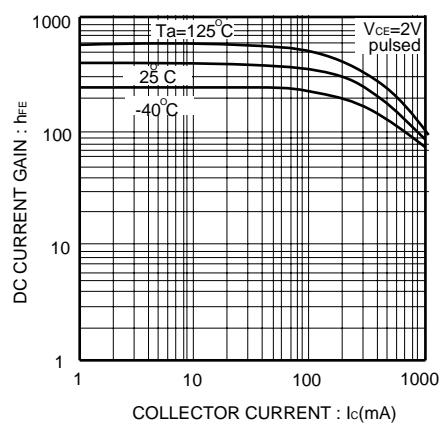


Fig.3 Collector-emitter saturation voltage vs. collector current (I)

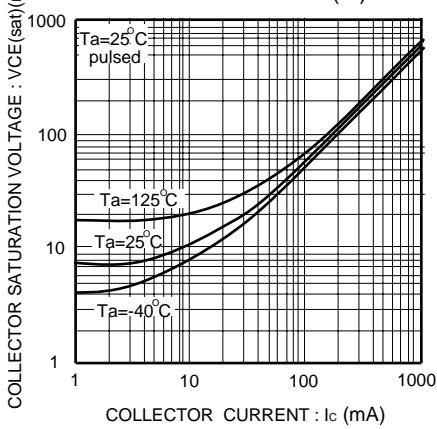
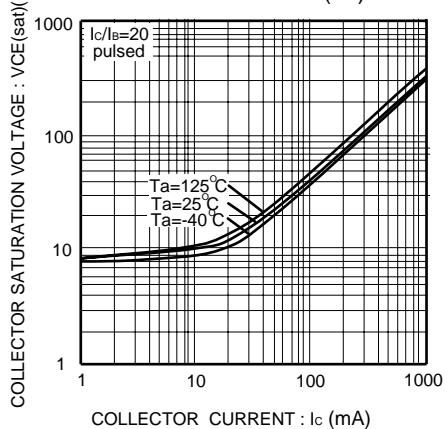


Fig.4 Collector-emitter saturation voltage vs. collector current (II)



RATING CHARACTERISTIC CURVES (CHUMF8PT)

2SC5585 Typical Electrical Characteristics

Fig.5 Base-emitter saturation voltage vs. collector current

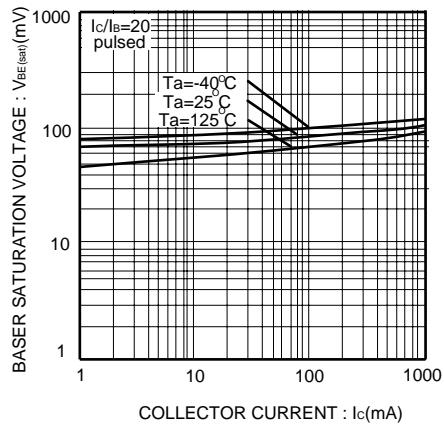


Fig.6 Gain bandwidth product vs. collector current

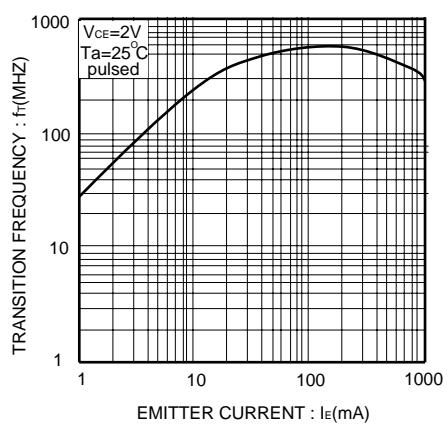
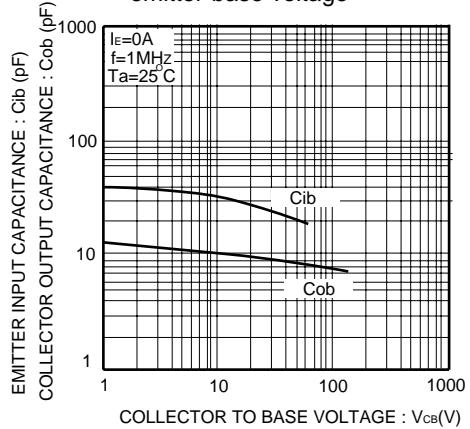


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage



RATING CHARACTERISTIC CURVES (CHUMF8PT)

CHDTC144E Typical Electrical Characteristics

Fig.1 Input voltage vs. output current
(ON characteristics)

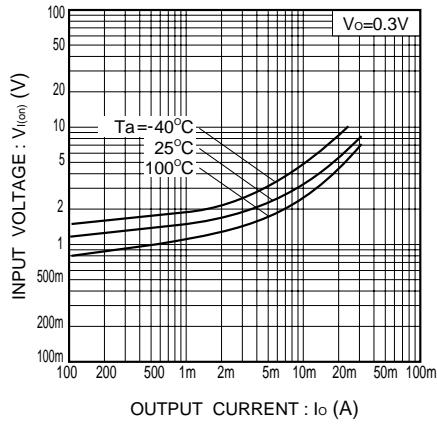


Fig.2 Output current vs. input voltage
(OFF characteristics)

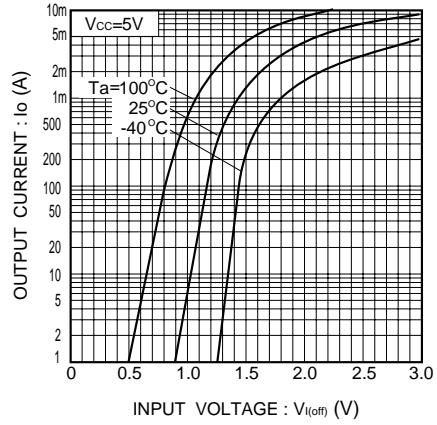


Fig.3 DC current gain vs. output current

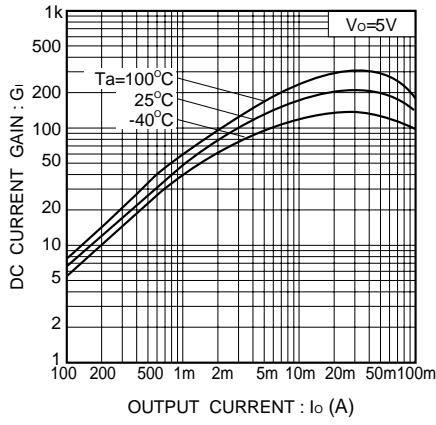


Fig.4 Output voltage vs. output current

